



BC847xMB series

45 V, 100 mA NPN general-purpose transistors

Rev. 1 — 5 March 2012

Product data sheet

1. Product profile

1.1 General description

NPN general-purpose transistors in a leadless ultra small SOT883B Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Package			PNP complement
	NXP	JEITA	JEDEC	
BC847AMB	SOT883B	-	-	BC857AMB
BC847BMB	SOT883B	-	-	BC857BMB
BC847CMB	SOT883B	-	-	BC857CMB

1.2 Features and benefits

- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm
- Power dissipation comparable to SOT23
- AEC-Q101 qualified

1.3 Applications

- General-purpose switching and amplification
- Mobile applications

1.4 Quick reference data

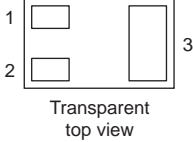
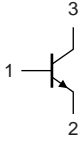
Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	45	V
I_C	collector current		-	-	100	mA
h_{FE}	DC current gain	$V_{CE} = 5\text{ V}; I_C = 2\text{ mA}$				
	BC847AMB		110	-	220	
	BC847BMB		200	-	450	
	BC847CMB		420	-	800	



2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	base		
2	emitter		
3	collector		

sym021

3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
BC847xMB series -		leadless ultra small plastic package; 3 solder lands; body 1.0 × 0.6 × 0.37 mm	SOT883B

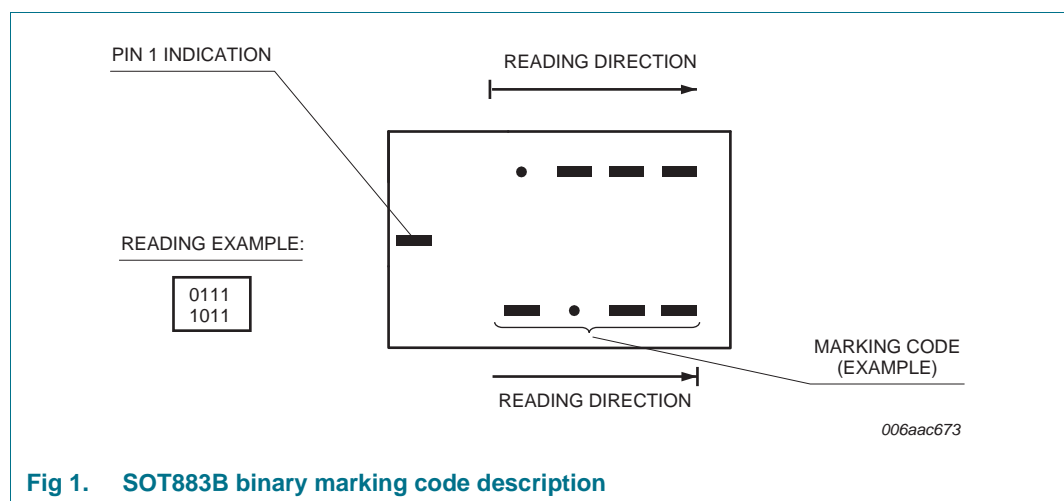
4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
BC847AMB	0100 0001
BC847BMB	0100 0010
BC847CMB	0100 0011

[1] For SOT883B binary marking code description, see [Figure 1](#).

4.1 Binary marking code description



5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	50	V
V_{CEO}	collector-emitter voltage	open base	-	45	V
V_{EBO}	emitter-base voltage	open collector	-	6	V
I_C	collector current		-	100	mA
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	200	mA
I_{BM}	peak base current	single pulse; $t_p \leq 1$ ms	-	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1][2] -	250	mW
T_j	junction temperature		-	150	°C
T_{amb}	ambient temperature		-55	+150	°C
T_{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1][2] -	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

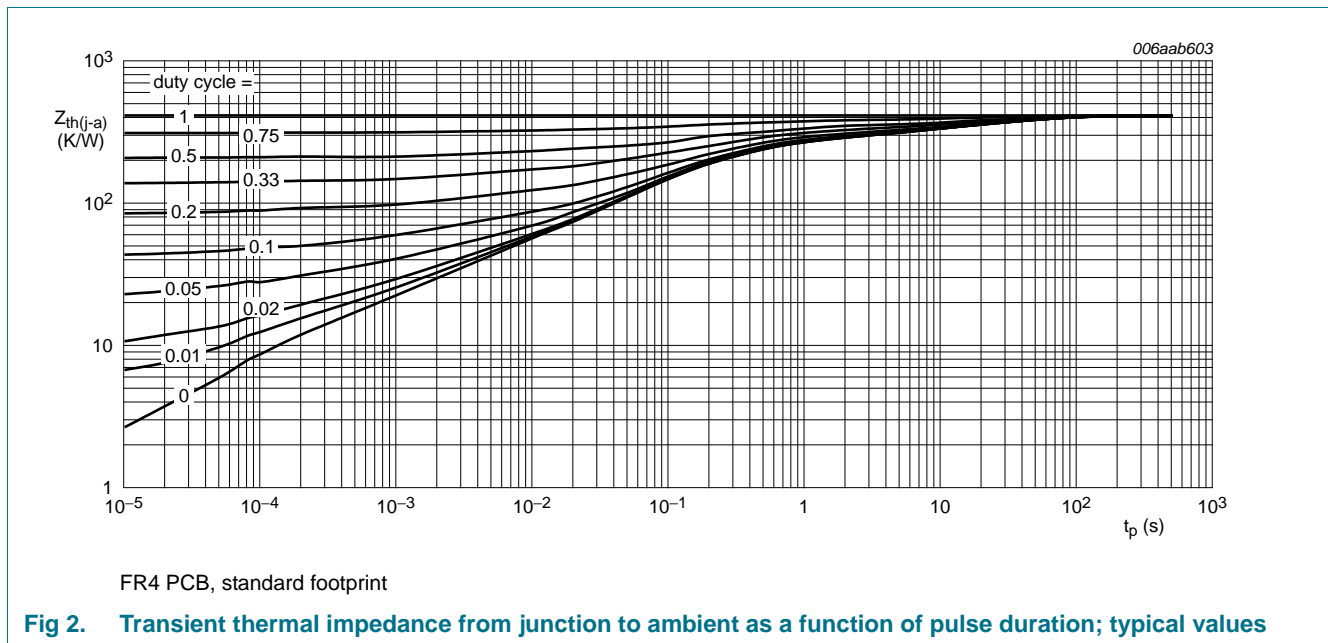


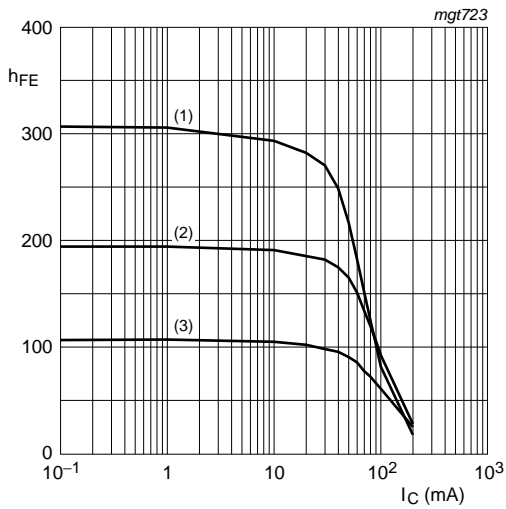
Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 8. Characteristics
 $T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

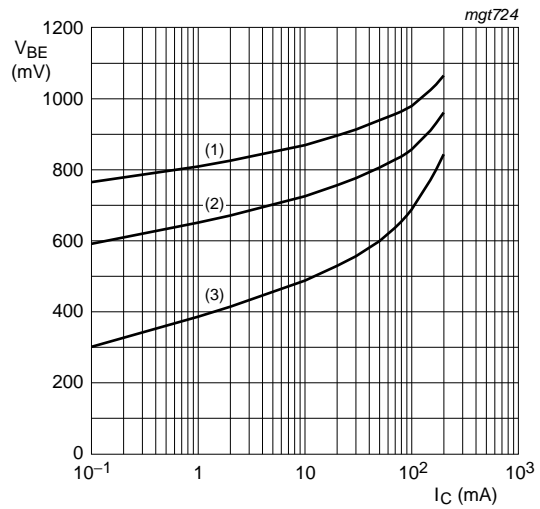
Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
I_{CBO}	collector-base cut-off current	$V_{CB} = 30\text{ V}; I_E = 0\text{ A}$	-	-	15	nA	
		$V_{CB} = 30\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	5	μA	
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	-	-	100	nA	
h_{FE}	DC current gain	$V_{CE} = 5\text{ V}; I_C = 2\text{ mA}$					
			BC847AMB	110	-	220	
			BC847BMB	200	-	450	
			BC847CMB	420	-	800	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	-	90	200	mV	
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}$	[1]	-	200	400	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	-	700	-	mV	
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}$	[1]	-	900	-	mV
V_{BE}	base-emitter voltage	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$	580	660	700	mV	
		$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$	-	-	770	mV	
f_T	transition frequency	$V_{CE} = 5\text{ V}; I_C = 10\text{ mA}; f = 100\text{ MHz}$	100	-	-	MHz	
C_c	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_C = 0\text{ A}; f = 1\text{ MHz}$	-	-	1.5	pF	
C_e	emitter capacitance	$V_{EB} = 0.5\text{ V}; I_C = I_E = 0\text{ A}; f = 1\text{ MHz}$	-	11	-	pF	
NF	noise figure	$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega; f = 1\text{ kHz}; B = 200\text{ Hz}$	-	2	10	dB	

[1] Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$.



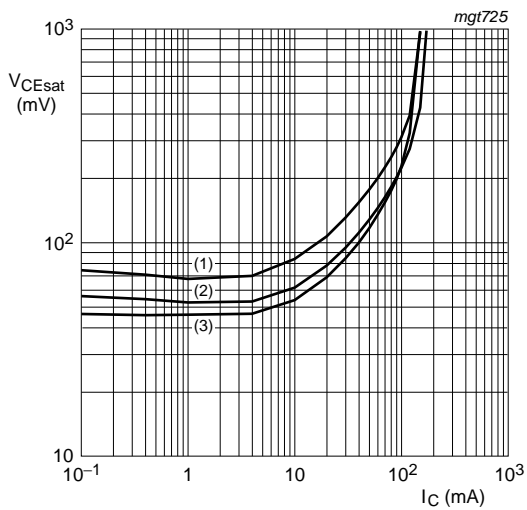
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 3. BC847AMB: DC current gain as a function of collector current; typical values



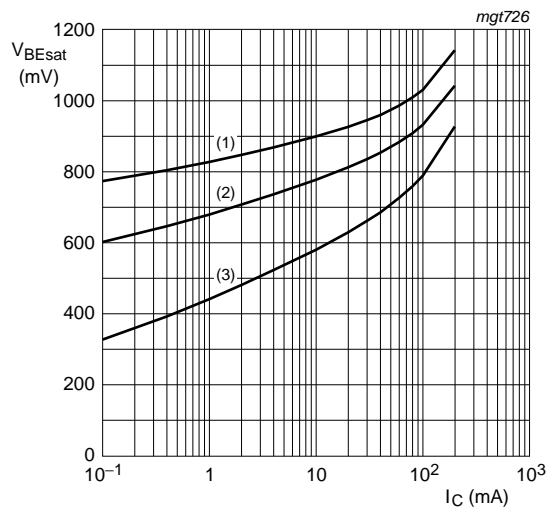
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = -55\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = 150\text{ }^{\circ}\text{C}$

Fig 4. BC847AMB: Base-emitter voltage as a function of collector current; typical values



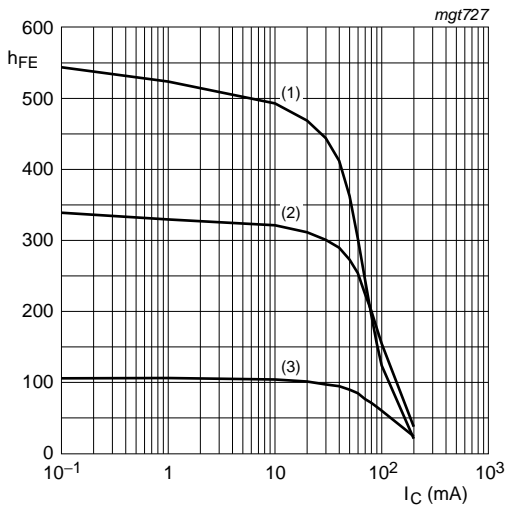
$I_C/I_B = 20$
 (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 5. BC847AMB: Collector-emitter saturation voltage as a function of collector current; typical values



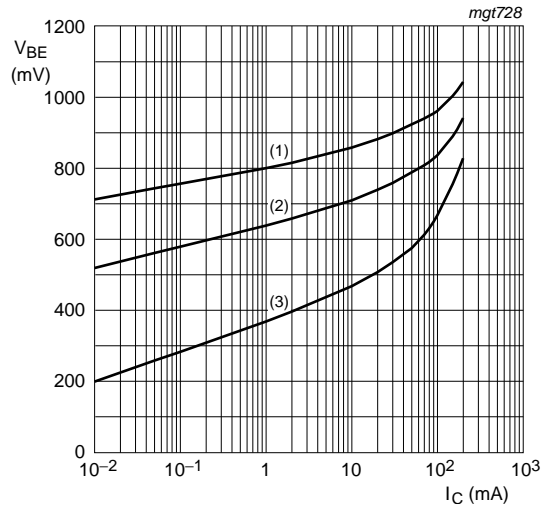
$I_C/I_B = 10$
 (1) $T_{amb} = -55\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = 150\text{ }^{\circ}\text{C}$

Fig 6. BC847AMB: Base-emitter saturation voltage as a function of collector current; typical values



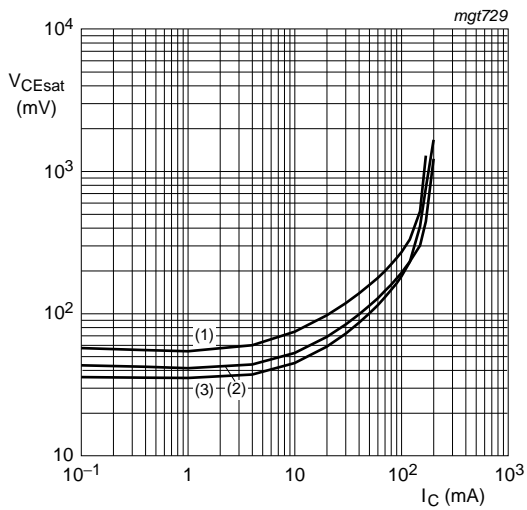
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = 150\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 7. BC847BMB: DC current gain as a function of collector current; typical values



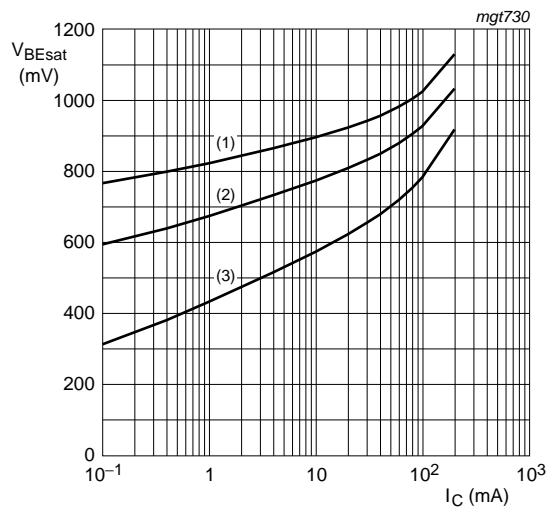
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 150\text{ °C}$

Fig 8. BC847BMB: Base-emitter voltage as a function of collector current; typical values



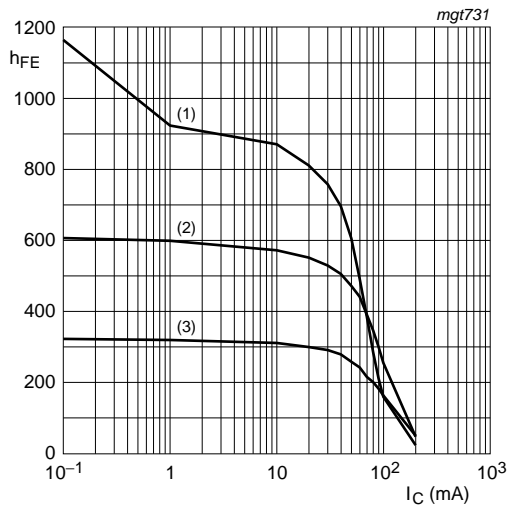
$I_C/I_B = 20$
 (1) $T_{amb} = 150\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 9. BC847BMB: Collector-emitter saturation voltage as a function of collector current; typical values



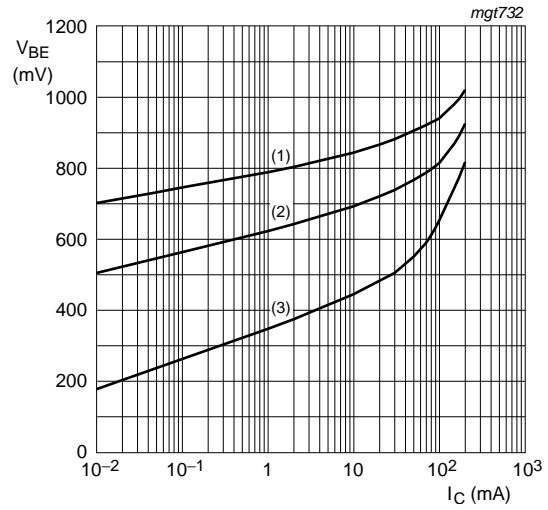
$I_C/I_B = 10$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 150\text{ °C}$

Fig 10. BC847BMB: Base-emitter saturation voltage as a function of collector current; typical values



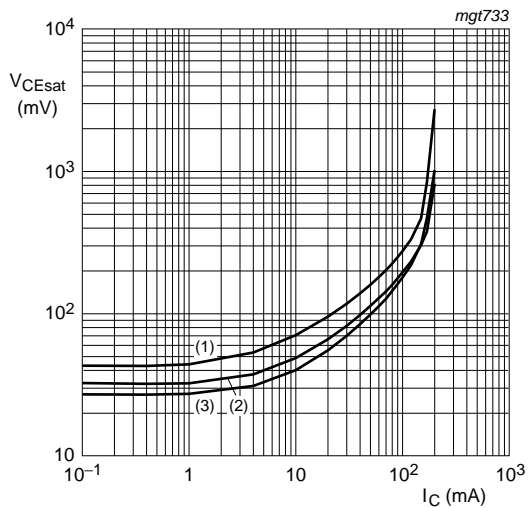
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = 150\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 11. BC847CMB: DC current gain as a function of collector current; typical values



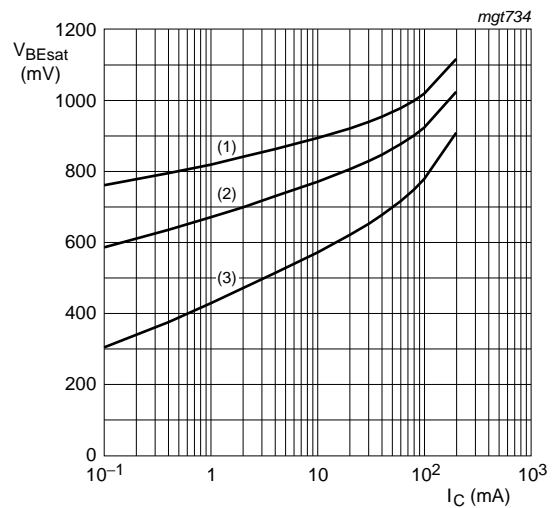
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 150\text{ °C}$

Fig 12. BC847CMB: Base-emitter voltage as a function of collector current; typical values



$I_C/I_B = 20$
 (1) $T_{amb} = 150\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 13. BC847CMB: Collector-emitter saturation voltage as a function of collector current; typical values



$I_C/I_B = 10$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 150\text{ °C}$

Fig 14. BC847CMB: Base-emitter saturation voltage as a function of collector current; typical values

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline

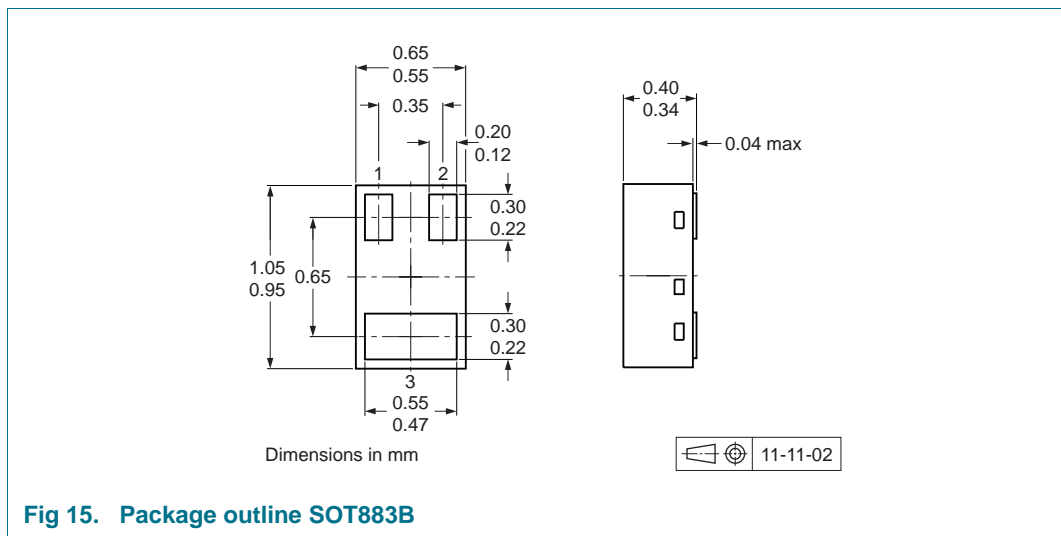


Fig 15. Package outline SOT883B

10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

Type number	Package	Description	Packing quantity
			10000
BC847xMB series	SOT883B	2 mm pitch, 8 mm tape and reel	-315

[1] For further information and the availability of packing methods, see [Section 14](#).

12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BC847XMB_SER v.1	20120305	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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